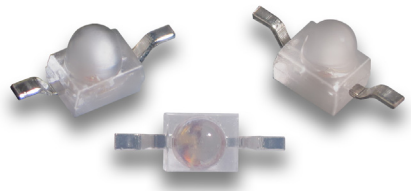
AM2520SF3C09-100MAV

Infrared Emitting Diode



DESCRIPTION

- SF3 made with AlGaAs on Si-substrate Infrared Emitting Diode

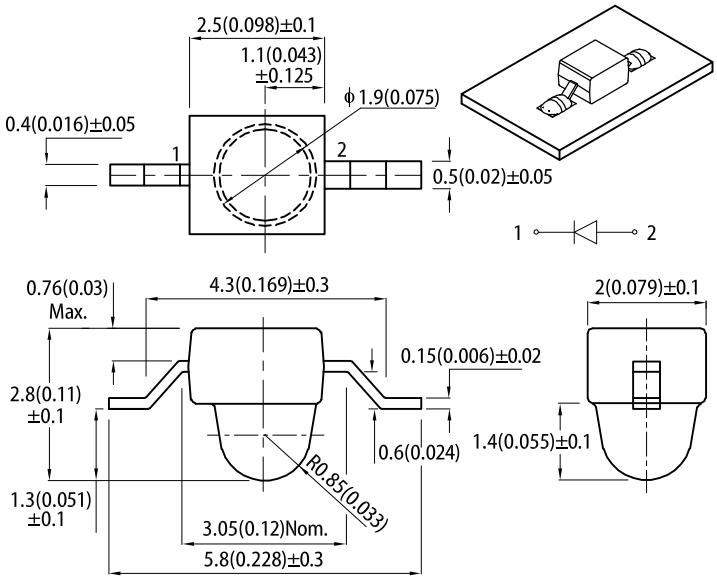
FEATURES

- Subminiature package
- Mechanically and spectrally matched to the Phototransistor
- High radiant power and high speed
- Package matches with photodetector AM2520PD1BT09
- Z-bend lead
- Long life - solid state reliability
- Low package profile
- Moisture sensitivity level: 3
- Package: 1000 pcs / reel
- Halogen-free
- RoHS compliant

APPLICATIONS

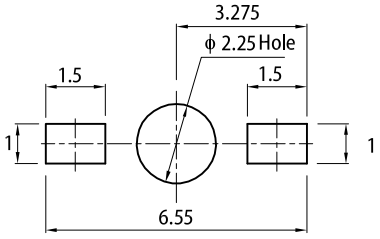
- Infrared Illumination for cameras
- Machine vision systems
- Surveillance systems
- Industrial electronics
- IR data transmission
- Remote control

PACKAGE DIMENSIONS



RECOMMENDED SOLDERING PATTERN

(units : mm; tolerance : ± 0.1)



Notes:
1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25(0.01") unless otherwise noted.
3. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.
4. The device has a single mounting surface. The device must be mounted according to the specifications.

SELECTION GUIDE

Part Number	Emitting Color (Material)	Lens Type	Po (mW/sr) @ 100mA [2]		Viewing Angle [1]
			Min.	Typ.	2θ1/2
AM2520SF3C09-100MAV	Infrared (AlGaAs)	Water Clear	80	120	20°

Notes:
1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 of the optical peak value.
2. Radiant Intensity / luminous flux: +/-15%.
3. Radiant intensity value is traceable to CIE127-2007 standards.

ELECTRICAL / OPTICAL CHARACTERISTICS at T_A=25°C

Parameter	Symbol	Emitting Color	Value		Unit
			Typ.	Max.	
Wavelength at Peak Emission I_F = 100mA	λ_{peak}	Infrared	940	-	nm
Spectral Bandwidth at 50% Φ REL MAX I_F = 100mA	Δλ	Infrared	48	-	nm
Forward Voltage I_F = 100mA	V_F [1]	Infrared	1.55	1.8	V
Reverse Current (V_R = 5V)	I_R	Infrared	-	10	μA
Rise Time I_F = 100mA	t_r	Infrared	10.6	-	ns
Fall Time I_F = 100mA	t_f	Infrared	10.3	-	ns
Temperature Coefficient of Wavelength I_F = 100mA, -10°C ≤ T ≤ 85°C	TC_λ	Infrared	0.3	-	nm/°C
Temperature Coefficient of V_F I_F = 100mA, -10°C ≤ T ≤ 85°C	TC_V	Infrared	-1.4	-	mV/°C

Notes:
1. Forward voltage: ±0.1V.
2. Wavelength value is traceable to CIE127-2007 standards.
3. Excess driving current and / or operating temperature higher than recommended conditions may result in severe light degradation or premature failure.

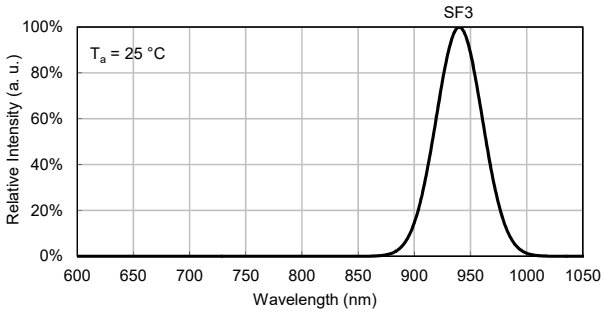
ABSOLUTE MAXIMUM RATINGS at T_A=25°C

Parameter	Symbol	Value	Unit
Power Dissipation	P_D	180	mW
Reverse Voltage	V_R	5	V
Junction Temperature	T_j	115	°C
Operating Temperature	T_{op}	-40 to +85	°C
Storage Temperature	T_{stg}	-40 to +85	°C
DC Forward Current	I_F	100	mA
Peak Forward Current	I_{FP} [1]	1200	mA
Electrostatic Discharge Threshold (HBM)	-	8000	V
Thermal Resistance (Junction / Ambient)	$R_{th\ JA}$ [2]	250	°C/W
Thermal Resistance (Junction / Solder point)	$R_{th\ JS}$ [2]	180	°C/W

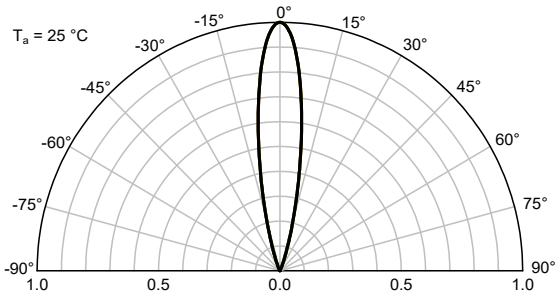
Notes:
1. 1/100 Duty Cycle, 10μs Pulse Width.
2. $R_{th\ JA}$,$R_{th\ JS}$ Results from mounting on PC board FR4 (pad size ≥ 16 mm^2 per pad).
3. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

TECHNICAL DATA

RELATIVE INTENSITY vs. WAVELENGTH

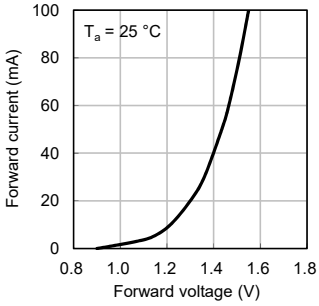


SPATIAL DISTRIBUTION

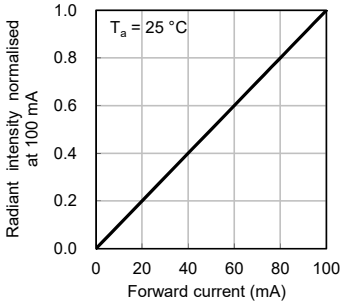


INFRARED

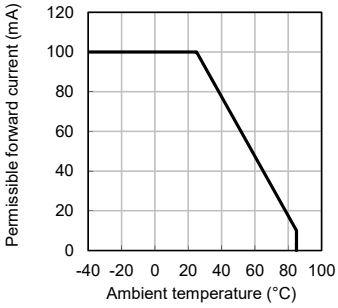
Forward Current vs. Forward Voltage



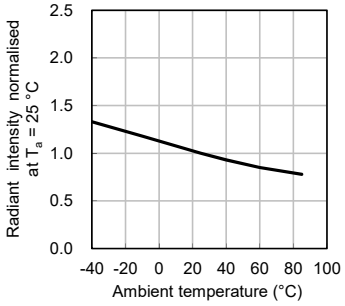
Radiant Intensity vs. Forward Current



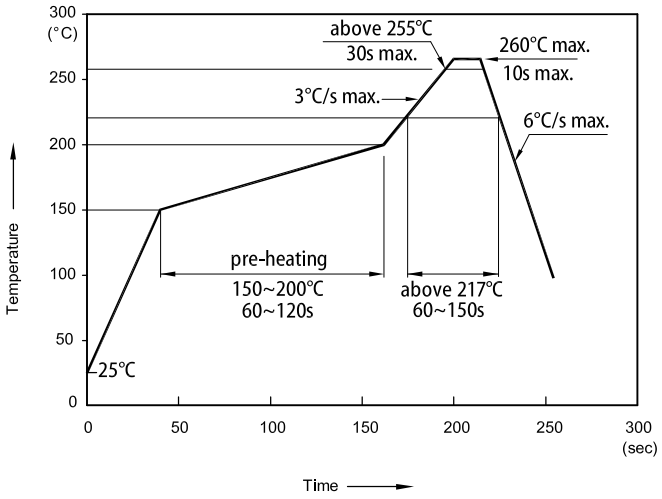
Forward Current Derating Curve



Radiant Intensity vs. Ambient Temperature

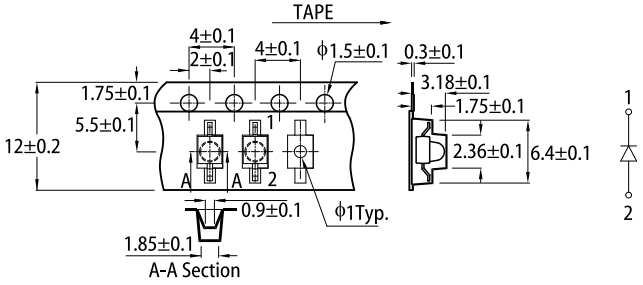


REFLOW SOLDERING PROFILE for LEAD-FREE SMD PROCESS

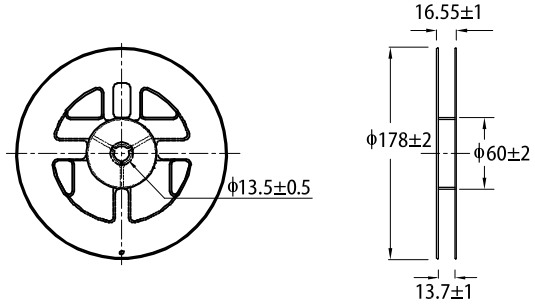


Notes:
1. Don't cause stress to the LEDs while it is exposed to high temperature.
2. The maximum number of reflow soldering passes is 2 times.
3. Reflow soldering is recommended. Other soldering methods are not recommended as they might cause damage to the product.

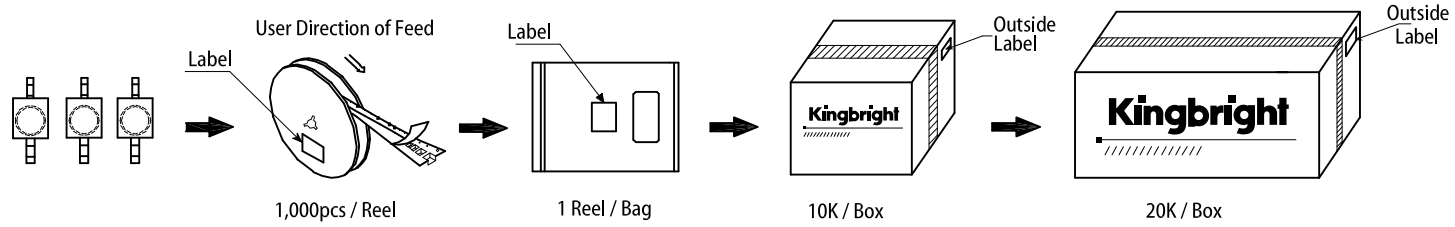
TAPE SPECIFICATIONS (units : mm)

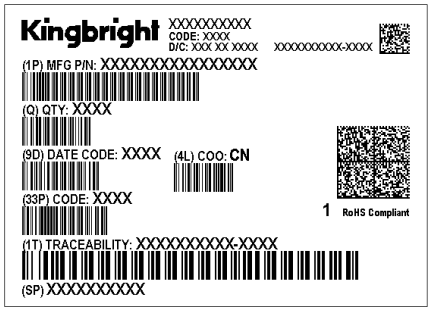


REEL DIMENSION (units : mm)



PACKING & LABEL SPECIFICATIONS





PRECAUTIONARY NOTES

1. The information included in this document reflects representative usage scenarios and is intended for technical reference only.
2. The part number, type, and specifications mentioned in this document are subject to future change and improvement without notice. Before production usage customer should refer to the latest datasheet for the updated specifications.
3. When using the products referenced in this document, please make sure the product is being operated within the environmental and electrical limits specified in the datasheet. If customer usage exceeds the specified limits, Kingbright will not be responsible for any subsequent issues.
4. The information in this document applies to typical usage in consumer electronics applications. If customer's application has special reliability requirements or have life-threatening liabilities, such as automotive or medical usage, please consult with Kingbright representative for further assistance.
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